Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
Tech ID: 24136 / UC Case 2009-742-0

BRIEF DESCRIPTION
An efficient method to significantly reduce defects in non-polar and semi-polar group-III nitride films.

BACKGROUND
The usefulness of non-polar and semi-polar group-III nitrides such as gallium nitride (GaN) and its alloys has been well established for its use in the fabrication of optoelectronic and high-powered electronic devices. Given recent trends in industry standards there is considerable interest in the growth of nonpolar (a- and m-plane) GaN based epitaxial films. The problems associated with the growth of these nonpolar GaN based films is characterized by high defect density, reduced carrier mobility, and low reliability which all contribute to an overall lower efficiency. However, high performance devices can be achieved by eliminating these defects by improving the structural quality of the nonpolar GaN films.

DESCRIPTION
Researchers at the University of California, Santa Barbara have developed an efficient method to significantly reduce defects in non-polar and semi-polar group-III nitride films. Through the use of in-situ SiNx as a nanomask when growing GaN substrates, researchers have demonstrated reduced stacking fault density, reduced thread dislocation density, reduced surface roughness, reduced sub-micron pits, and increased luminescence. Compared to the lateral epitaxial overgrowth (LEO) technique, this invention has the advantage of being a simple process that avoids contamination characteristic of the ex-situ process used in LEO. Unlike LEO, this new process also facilitates nanometer scale lateral epitaxial overgrowth at the open pores of the film which reduces the differences between the wing and window regions of film which has adverse effects on devices if untreated. All structure improvements contribute to an overall reduction of defects uniformly across the film which significantly increases the efficiency of the material.

ADVANTAGES
▶ Uniform defect reduction across film
▶ Highly efficient process capable of being done on the nanometer scale
▶ Improved performance of semi-polar and non-polar group-III nitride based devices
▶ Highly adaptable and easily controllable process

APPLICATIONS
▶ LDs and LEDs
▶ Group-III nitride materials
▶ High powered electronic and optoelectronic devices

OTHER INFORMATION
KEYWORDS
indSSL, indLED, LED, group-III nitrides, misfit dislocation

CATEGORIZED AS
▶ Engineering
▶ Energy
▶ Lighting
▶ Semiconductors
▶ Design and Fabrication

RELATED CASES
2009-742-0

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PATENT STATUS
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ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Method for Improved Surface of (Ga,Al,In,B)N Films on Nonpolar or Semipolar Substrates
- High Efficiency LED with Optimized Photonic Crystal Extractor
- Enhanced Optical Polarization of Nitride LEDs by Increased Indium Incorporation
- Edge-Emitting Laser Diode with Via-Activated Tunnel Junction Contact
- Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
- Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
- Flexible Arrays of MicroLEDs using the Photoelectrochemical (PEC) Lift-off Technique
- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- Gallium-containing MicroLEDs for Displays
- High Speed Indium Gallium Nitride Multi-Quantum Well (InGaN MQW) Photodetector
- Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
- Internal Heating for Ammonothermal Growth of Group-III Nitride Crystals
- Defect Reduction in GaN films using in-situ SiNx Nanomask
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Highly Efficient Blue-Violet III-Nitride Semipolar Laser Diodes
- Hybrid Growth Method for Improved III-Nitride Tunnel Junction Devices
- Phosphor-Free White Light Source
- Volumetric Hole Injection with Intentional V-Defects
- Control of Photoelectrochemical (PEC) Etching by Modification of the Local Electrochemical Potential of the Semiconductor Structure
- Low Temperature Deposition of Magnesium Doped Nitride Films
- Transparent Mirrorless (TML) LEDs
- Improved GaN Substrates Prepared with Ammonothermal Growth
- Laser Diode With Tunnel Junction Contact Surface Grating
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- High Efficiency Semipolar AlGaN-Cladding-Free Laser Diodes
- Method for Growing Self-Assembled Quantum Dot Lattices
- Method for Enhancing Growth of Semipolar Nitride Devices
- III-Nitride Tunnel Junction with Modified Interface
- Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
- Nonpolar III-Nitride LEDs With Long Wavelength Emission
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- Increased Light Extraction with Multistep Deposition of ZnO on GaN
- Method for Manufacturing Improved III-Nitride LEDs and Laser Diodes: Monolithic Integration of Optically Pumped and Electrically Injected III-Nitride LEDs
- Selective-Area Mesoporous Semiconductors And Devices For Optoelectronic And Photonic Applications
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Method for Growing High-Quality Group III-Nitride Crystals
- Near-Infrared, Flip-Chip, TCO-Clad, InGaN Quantum Dot Laser Diode
- Incorporating Temperature-Sensitive Layers in III-N Devices
- Oxyfluoride Phosphors for Use in White Light LEDs
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,AJ)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
- Heterogeneously Integrated GaN on Si Photonic Integrated Circuits
- (Al, In,Ga, B)N Device Structures
- Reduction in Leakage Current and Increase in Efficiency of III-Nitride MicroLEDs
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- 3D Hole Injectors for InAlGaN Light-Emitting Diodes
- Formation of Transparent Integrated MicroLED Displays
- Low-Droop LED Structure on GaN Semi-polar Substrates
Contact Architectures for Tunnel Junction Devices
Photoelectrochemical Etching Of P-Type Semiconductor Heterostructures
Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
Growth of Semipolar III-V Nitride Films with Lower Defect Density
III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
In-Situ Methods Of Preventing Interfacial Impurities And Dry Etch-Induced Damage In Regrown III-Nitride Structures
Enhanced Hole Injection by P-Type Active Region and Lateral Injection in InAlGaN LEDs
Improved Manufacturing of Solid State Lasers via Patternning of Photonic Crystals
Solid Solution Phosphors for Use in Solid State White Lighting Applications
Multifaceted III-Nitride Surface-Emitting Laser
Tunable White Light Based on Polarization-Sensitive LEDs
Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
III-Nitride VCSEL with a High Indium Content Active Region
Growth of High-Performance M-plane GaN Optical Devices
Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
Improved Anisotropic Strain Control in Semipolar Nitride Devices
High Light Extraction Efficiency III-Nitride LED
Photoelectrochemical Etching for Chip Shaping Of LEDs
III-V Nitride Device Structures on Patterned Substrates
Hexagonal Wurtzite Type Epitaxial Layer with a Low Alkali-Metal Concentration
Method for Increasing GaN Substrate Area in Nitride Devices
Burying Impurities And Defects In Regrown III-Nitride Structures
Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
Single or Multi-Color High Efficiency LED by Growth Over a Patterned Substrate
GaN-Based Thermoelectric Device for Micro-Power Generation
Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patternning
Improved Manufacturing of Semiconductor Lasers
LED Device Structures with Minimized Light Re-Absorption
Improved Light Extraction with Geometrically Tuned LED Arrays
Growth of Planar Semi-Polar Gallium Nitride
Nonpolar (Al, B, In, Ga)N Quantum Well Design
UV Optoelectronic Devices Based on Nonpolar and Semi-polar AlInN and AlInGaN Alloys
Defect Reduction of Non-Polar and Semi-Polar III-Nitrides
III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-150)
Suppression of Defect Formation and Increase in Critical Thickness by Silicon Doping
Wafer Bonding for Embedding Active Regions with Relaxed Nanofeatures
Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD